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Education

B.S. 1983.3 ~ 1987.2	Dept. of Physics, Seoul National University, Seoul, Korea
M.S. 1987.3 ~ 1989.5	Dept. of Physics, The University of Michigan, Ann Arbor, Michigan
Ph.D. 1990.9 ~ 1995.5	School of Applied and Engineering Physics, Cornell University, Ithaca, New York
	Advisor: Lester F. Eastman

Experiences

Jul. 1995 -Aug. 1996	Postdoctoral Associate, School of Electrical Engineering, Cornell University, USA
Sep. 1996-Feb. 1998	PMTS, Bell Labs, Lucent Technologies, Murray Hill, NJ, USA
Mar. 1998-present	Assistant/Associate/Full Professor,
	Dept. of Electronic Engineering, Sogang University, Seoul, Korea
Aug. 2006- Jul. 2007	Principal Scientist, Pixelplus Semiconductor, San Jose, CA, USA.

Activities:

2000 AP-ASIC (Asia-Pacific Conference on Advanced System ICs), Cheju, Korea

Technical Program Committee Secreatry

2004 AP-ASIC (Asia-Pacific Conference on Advanced System ICs), Fukuoka, Japan

Technical Program Committee Co-chair

2014 ISOCC (International SoC Design Conference), Seoul, Korea, Technical Program Chair

2015 ISOCC (International SoC Design Conference), Seoul, Korea, General Chair

2021 ISCAS (International Symposium on Circuits and Systems) General Chair

IEIE (THE INSTITUTE OF ELECTRONICS AND INFORMATION ENGINEERS) a member in the Board of Directors

Research Interests:

- CMOS and BiCMOS Wireless Communication Circuits
  - Research project on 5-6 GHz on transceiver IC from Samsung Electronics
- Optical Fiber Communication Circuits
  - Pre-Amplifiers, Limiting Amps, Laser Drivers, CDRs
  - Research projects from Korean Government

SELECTED PUBLICATIONS

Journal Publications

S.D. Peacor, R.A. Richardson, **J. Burm**, C. Uher, and A.B. Kaiser, "Thermal Conductivity of Ba-K-Bi-O: A Contrast to Copper Oxide Superconductors," *Physical Review B* (Condensed Matter), vol. 42, pp. 2684-2687 (1990).

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M.A. Khan, Q. Chen, M.S. Shur, B.T. Dermott, J.A. Higgins, **J. Burm**, W.J. Schaff, L.F. Eastman, "CW Operation of Short-Channel GaN/AlGaN Doped Channel Heterostructure Field Effect Transistors at 10 GHz and 15 GHz," IEEE Electron Device Letters, vol. 17, no. 12, pp. 584-585 (1996).

L. Eastman, **J. Burm,** W. Schaff, M. Murphy, K. Chu, H. Amano, and I. Akasaki, "Research on GaN MODFET's," Material Research Society Internet Journal, Nitirde of Semiconductor Research, vol. 1, no. 4, http://nsr.mij.mrs.org/1/ (1996).

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Junan Lee, Himchan Park, Bongsub Song, Kiwoon Kim, Jaeha Eom, Kyunghoon Kim and Jinwook Burm,"High Frame Rate VGA CMOS Image Sensor using Non-Memory Capacitor Two-Step Single Slope ADCs," IEEE TRANSACTIONS ON CIRCUITS AND SYSTEMS I, VOL. 62, NO. 9, pp. 2147-2154, 2015.

Qiwei Haung, Hyobin Joo, Jinwoo Kim, Chenchang Zhan, Jinwook Burm,"An Energy-Efficient Frequency Domain CMOS Temperature Sensor with Switched Vernier Time-to-Digital Conversion," 2017 Sensors Journal, VOL. 17, NO. 10, pp. 3001-3011, 2017.

Patents

J. Burm, R. A. Hamm, R. F. Kopf, R. W. Ryan, A. Tate, "Alignment Techniques for Photolithography utilizing Multiple Photoresist Layers," US6,042,975, Lucent Tech, 2000.

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L. F. Eastman, K. Litvin **J. Burm**, D.W. Woodard and W.J. Schaff, "High Frequency Optical Receivers," *2nd Annual DARPA/Rome Lab. Symp. on Photonics Systems for Antenna Applications (PSSA)*, Monterey, CA (Dec. 10-12, 1991).

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